12500 TI Boulevard, MS 8640, Dallas, Texas 75243

PCN# 20260414002.2
Qualification of MIHO using qualified Process Technology and additional Assembly site for select devices
Change Notification / Sample Request

Date: April 15, 2026
To: MOUSER PCN

Dear Customer:

This is an announcement of a change to a device that is currently offered by Texas Instruments. The details of this change are on the following pages.

Texas Instruments requires acknowledgement of receipt of this notification within 60 days of the date of this notice. Lack of acknowledgement of this notice within 60 days constitutes acceptance and approval of this change. If samples or additional data are required, requests must be received within 60 days of this notification.

The changes discussed within this PCN will not take effect any earlier than the proposed first ship date on Page 3 of this notification, unless customer agreement has been reached on an earlier implementation of the change.

This notice does not change the end-of-life status of any product. Should product affected be on a previously issued product withdrawal/discontinuance notice, this notification does not extend the life of that product or change the life time buy offering/discontinuance plan.

For questions regarding this notice or to provide acknowledgement of this PCN, you may contact your local Field Sales Representative or the change management team.

For sample requests or sample related questions, contact your local Field Sales Representative.

TI values customer engagement and feedback related to TI changes. Customers should contact TI if there are questions or concerns regarding a change notification.

Sincerely,

Change Management Team
SC Business Services

20260414002.2
Change Notification / Sample Request
Attachments

Products Affected:

The devices listed on this page are a subset of the complete list of affected devices. According to our records**,** you have recently purchased these devices**.** The corresponding customer part number is also listed, if available.

DEVICE	CUSTOMER PART NUMBER
ESD2CAN36DBZRQ1	NULL
ESD2CANFD36DBZRQ1	NULL

Technical details of this Product Change follow on the next page(s).

PCN Number:	20260414002.2	**PCN Date:**	April 15, 2026
Title:	Qualification of MIHO using qualified Process Technology and additional Assembly site for select devices		
Customer Contact:	Change Management team	**Dept:**	Quality Services
Proposed 1st Ship Date:	October 12, 2026	**Sample requests accepted until:**	June 14, 2026

***Sample requests received after** June 14, 2026 **will not be supported.**

Change Type:

☒	Assembly Site	☐	Design	☐	Wafer Bump Material
☐	Assembly Process	☐	Data Sheet	☐	Wafer Bump Process
☒	Assembly Materials	☐	Part number change	☒	Wafer Fab Site
☐	Mechanical Specification	☒	Test Site	☐	Wafer Fab Material
☒	Packing/Shipping/Labeling	☐	Test Process	☐	Wafer Fab Process

PCN Details

Description of Change:

Texas Instruments is pleased to announce the addition of MIHO using the VDIODE qualified process technology and CDAT Assembly Site for the devices listed below.

Current Fab Site			Additional Fab Site		
Current Fab Site	**Process**	**Wafer Diameter**	**Additional Fab Site**	**Process**	**Wafer Diameter**
CFAB	VDIODE	200 mm	MIHO	VDIODE	200 mm

Construction differences are as follows:

	Current	**Additional**
Assembly Site	**TIPI**	**CDAT**
Lead Finish	NiPdAu	Matte Sn
Mount compound	4226215	4229877

Qual details are provided in the Qual Data Section.

Reason for Change:

Continuity Supply

Anticipated impact on Form, Fit, Function, Quality or Reliability (positive / negative):

Review the updated Standard Data Packet for more details on the changes.

Impact on Environmental Ratings:

Checked boxes indicate the status of environmental ratings following implementation of this change. If below boxes are checked, there are no changes to the associated environmental ratings.

RoHS	REACH	Green Status	IEC 62474
☒ No Change	☒ No Change	☒ No Change	☒ No Change

Changes to product identification resulting from this PCN:

Fab Site Information:

Chip Site	Chip Site Origin Code (20L)	Chip Site Country Code (21L)	Chip Site City

CFAB	CU3	CHN	CHENGDU
MIHO	**MH8**	**JPN**	**Miho, Ibaragi-ken**

Assembly Site Information:

Assembly Site	Assembly Site Origin (22L)	Assembly Country Code (23L)	Assembly City
TIPI	PHI	PHL	Baguio City
CDAT	**CDA**	**CHN**	**Chengdu**

Sample product shipping label (not actual product label):

Product Affected: Fab and A/T

ESD2CAN36DBZRQ1 ESD2CANFD36DBZRQ1

Qualification Data

Qualification Report

VDIODE: Transfer from CFAB to MIHO. Qual Driver 3: TSM36ADBZR Approve Date 01-October-2025

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

Type	#	Test Name	Condition	Duration	Qual Device: TSM36ADBZR	QBS Reference: ESD2CAN24DBZRQ1
HAST	A2	Biased HAST	130C/85%RH	96 Hours	-	2/154/0
UHAST	A3	Unbiased HAST	130C/85%RH	96 Hours	-	2/154/0
TC	A4	Temperature Cycle	-65C/150C	500 Cycles	-	2/154/0
HTOL	B1	High Temperature Reverse Bias	125C	1000 Hours	1/77/0	-
HTOL	B1	High Temperature Reverse Bias	125C	2000 Hours	-	2/154/0
SD	C3	PB Solderability	Precondition w.155C Dry Bake (4 hrs +/- 15 minutes)	-	-	1/10/0
SD	C3	PB-Free Solderability	Precondition w.155C Dry Bake (4 hrs +/- 15 minutes)	-	-	1/15/0
PD	C4	Physical Dimensions	Cpk>1.67	-	-	2/60/0
ESD	E2	ESD CDM	-	750 Volts	-	1/10/0
ESD	E2	ESD HBM	-	2000 Volts	-	1/10/0
CHAR	E5	Electrical Distributions	Cpk>1.67 Room, hot, and cold	-	-	2/50/0

QBS: Qual By Similarity, also known as Generic Data
Qual Device TSM36ADBZR is qualified at MSL1 260C

- Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable
- The following are equivalent HTOL options based on an activation energy of 0.7eV : 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours
- The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours
- The following are equivalent Temp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles

Quality and Environmental data is available at TI's external Web site: http://www.ti.com/

TI Qualification ID: R-CHG-2409-081

Automotive DBZ devices offload from TIPI to CDAT.
Approve Date 07-January-2025

Product Attributes

Attributes	Qual Device: ESD5452DBZRQ1	Qual Device: ESD652DBZRQ1	Qual Device: ESD2CANFD24DBZRQ1	Qual Device: ESD2CANXL24DBZRQ1	Qual Device: ESD2CAN24DBZRQ1	Qual Device: ESD2CANFD36DBZRQ1	Qual Device: ESD2CAN36DBZRQ1	QBS Reference: ESD2CAN24DBZRQ1
Automotive Grade Level	Grade 1	Grade 1	Grade 1	Grade 1	Grade 1	Grade 1	Grade 1	Grade 1
Operating Temp Range (C)	-40 to 125	-40 to 125	-40 to 125	-40 to 125	-40 to 125	-40 to 125	-40 to 125	-40 to 125
Product Function	Interface	Interface	Interface	Interface	Interface	Interface	Interface	Interface
Wafer Fab Supplier	CFAB	CFAB	CFAB	CFAB	CFAB	CFAB	CFAB	CFAB
Assembly Site	CDAT	CDAT	CDAT	CDAT	CDAT	CDAT	CDAT	PHI
Package Group	SOT	SOT	SOT	SOT	SOT	SOT	SOT	SOT
Package Designator	DBZ	DBZ	DBZ	DBZ	DBZ	DBZ	DBZ	DBZ
Pin Count	3	3	3	3	3	3	3	3

- QBS: Qual By Similarity, also known as Generic Data
- Qual Device ESD5452DBZRQ1 is qualified at MSL1 260C
- Qual Device ESD652DBZRQ1 is qualified at MSL1 260C
- Qual Device ESD2CANFD24DBZRQ1 is qualified at MSL1 260C
- Qual Device ESD2CANXL24DBZRQ1 is qualified at MSL1 260C
- Qual Device ESD2CAN24DBZRQ1 is qualified at MSL1 260C
- Qual Device ESD2CANFD36DBZRQ1 is qualified at MSL1 260C Qual Device ESD2CAN36DBZRQ1 is qualified at MSL1 260C

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

Type	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: ESD5452DBZRQ1	Qual Device: ESD652DBZRQ1	Qual Device: ESD2CANFD24DBZRQ1	Qual Device: ESD2CANXL24DBZRQ1	Qual Device: ESD2CAN24DBZRQ1	Qual Device: ESD2CANFD36DBZRQ1	Qual Device: ESD2CAN36DBZRQ1	QBS Reference: ESD2CAN24DBZRQ1
Test Group A - Accelerated Environment Stress Tests															
PC	A1	JEDEC J-STD-020 JESD22A113	-	0	Preconditioning	MSL1 260C	1 Step	-	-	-	1/0/0	-	1/0/0	1/0/0	3/Pass
HAST	A2	JEDEC JESD22A110	3	77	Biased HAST	130C/85%RH	96 Hours	1/77/0	-	-	1/77/0	-	-	1/77/0	3/231/0
HAST	A2.1	JEDEC JESD22-A110	3	77	Biased HAST	130C/85%RH	96 Hours	1/77/0	-	-	1/77/0	-	-	1/77/0	3/231/0
HAST	A2.1.2	-	3	1	Cross Section, post bHAST 1X	Post stress cross section	Completed	1/1/0	-	-	1/1/0	-	-	1/1/0	3/3/0

Type	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: ESD5452DBZRQ1	Qual Device: ESD652DBZRQ1	Qual Device: ESD2CANFD24DBZRQ1	Qual Device: ESD2CANXL24DBZRQ1	Qual Device: ESD2CAN24DBZRQ1	Qual Device: ESD2CANFD36DBZRQ1	Qual Device: ESD2CAN36DBZRQ1	QBS Reference: ESD2CAN24DBZRQ1
HAST	A2.1.3	-	3	3	Wire Bond Shear, post bHAST 1X	Post stress	-	1/3/0	-	-	1/3/0	-	-	1/3/0	3/9/0
HAST	A2.1.4	-	3	3	Bond Pull, exam Stitch, post bHAST 1X	Post stress	-	1/3/0	-	-	1/3/0	-	-	1/3/0	3/9/0
HAST	A2.1.5	-	3	3	Bond Pull, exam Ball, post bHAST 1X	Post stress	-	1/3/0	-	-	1/3/0	-	-	1/3/0	3/9/0
HAST	A2.2	JEDEC JESD22A110	3	70	Biased HAST	130C/85%RH	192 Hours	1/77/0	-	-	1/77/0	-	-	1/77/0	3/231/0
HAST	A2.2.1	-	3	22	SAM Analysis, post bHAST 2X	Review for delamination	Completed	1/22/0	-	-	1/22/0	-	-	1/22/0	3/66/0
HAST	A2.2.2	-	3	1	Cross Section, post bHAST 2X	Post stress cross section	Completed	1/1/0	-	-	1/1/0	-	-	1/1/0	3/3/0
HAST	A2.2.3	-	3	3	Wire Bond Shear, post bHAST 2X	Post stress	-	1/3/0	-	-	1/3/0	-	-	1/3/0	3/9/0
HAST	A2.2.4	-	3	3	Bond Pull, exam Stitch, post bHAST 2X	Post stress	-	1/3/0	-	-	1/3/0	-	-	1/3/0	3/9/0
HAST	A2.2.5	-	3	3	Bond Pull, exam Ball, post bHAST 2X	Post stress	-	1/3/0	-	-	1/3/0	-	-	1/3/0	3/9/0
AC/UHAST	A3	JEDEC JESD22A118	3	77	Unbiased HAST	130C/85%RH	96 Hours	-	-	-	1/77/0	-	1/77/0	1/77/0	3/231/0
TCHT	A4.1	JEDEC JESD22A104 and Appendix 6	3	77	Temperature Cycle	-65C/150C	1000 Cycles	-	-	-	1/77/0	-	1/77/0	1/77/0	3/231/0
TC	A4.1	JEDEC JESD22A104 and Appendix 3	3	77	Temperature Cycle	-65C/150C	500 Cycles	-	-	-	1/77/0	-	1/77/0	1/77/0	3/231/0
TC	A4.1.1	-	3	22	SAM Analysis, post TC 1X	Review for delamination	Completed	-	-	-	1/22/0	-	1/22/0	1/22/0	3/66/0
TC	A4.1.2	-	3	1	Cross Section, post TC, 1X	Post stress cross section	Completed	-	-	-	1/1/0	-	1/1/0	1/1/0	3/3/0
TC	A4.1.3	-	3	3	Wire Bond Shear, post TC, 1X	Post stress	-	-	-	-	1/3/0	-	1/3/0	1/3/0	3/9/0
TC	A4.1.4	-	3	3	Bond Pull, exam Stitch, post TC, 1X	Post stress	-	-	-	-	1/3/0	-	1/3/0	1/3/0	3/9/0

TC	A4.1.5	-	3	3	Bond Pull Lower Ball, post TC, 1X	Post stress	-	-	-	-	1/3/0	-	1/3/0	1/3/0	3/9/0
TC	A4.2	JEDEC JESD22A104 and Appendix 3	3	70	Temperature Cycle	-65C/150C	1000 Cycles	-	-	-	1/77/0	-	1/77/0	1/77/0	3/231/0
TC	A4.2.1	-	3	22	SAM Analysis, post TC, 2X	Review for delamination	Completed	-	-	-	1/22/0	-	1/22/0	1/22/0	3/66/0
TC	A4.2.2	-	3	1	Cross Section, post TC, 2X	Post stress cross section	Completed	-	-	-	1/1/0	-	1/1/0	1/1/0	3/3/0
TC	A4.2.3	-	3	3	Wire Bond Shear, post TC, 2X	Post stress	-	-	-	-	1/3/0	-	1/3/0	1/3/0	3/9/0
TC	A4.2.4	-	3	3	Bond Pull Lower Stitch, post TC, 2X	Post stress	-	-	-	-	1/3/0	-	1/3/0	1/3/0	3/9/0
Type	**#**	**Test Spec**	**Min Lot Qty**	**SS / Lot**	**Test Name**	**Condition**	**Duration**	**Qual Device: ESD545ZDBZRQ1**	**Qual Device: ESD652DBZRQ1**	**Qual Device: ESD2CANFD24DBZRQ1**	**Qual Device: ESD2CANXL24DBZRQ1**	**Qual Device: ESD2CAN24DBZRQ1**	**Qual Device: ESD2CANFD36DBZRQ1**	**Qual Device: ESD2CAN36DBZRQ1**	**QBS Reference: ESD2CAN24DBZRQ1**
TC	A4.2.5	-	3	3	Bond Pull Lower Ball, post TC, 2X	Post stress	-	-	-	-	1/3/0	-	1/3/0	1/3/0	3/9/0
Test Group B - Accelerated Lifetime Simulation Tests															
HTRB	B1.1	MIL-STD750-1	3	77	High Temperature Reverse Bias	125C	1000 Hours	-	-	-	-	-	-	-	3/231/0
HTRB	B1.2	MIL-STD750-1	3	77	High Temperature Reverse Bias	125C	2000 Hours	-	-	-	-	-	-	-	3/231/0
HTRB	B1	MIL-STD750-1	3	5	Post Temp Cycle Bond Pull	MIL-STD 883 Method 2011	1 Step	-	-	-	-	-	-	-	3/15/0
Test Group C - Package Assembly Integrity Tests															
DPA	C2	JESD22B100	-	30	Physical Dimensions	Cpk>1.67	1 Step	1/30/0	1/30/0	1/30/0	1/30/0	1/30/0	1/30/0	1/30/0	3/90/0
WBP	C3	MIL-STD750-2	-	10	Wire Bond Pull	Minimum of 5 devices, 30 wires Cpk>1.67	1 Step	1/10/0	1/10/0	1/10/0	1/10/0	1/10/0	1/10/0	1/10/0	3/30/0
WBS	C4	AECQ101-003	-	10	Wire Bond Shear	Minimum of 5 devices, 30 wires Cpk>1.67	1 Step	1/10/0	1/10/0	1/10/0	1/10/0	1/10/0	1/10/0	1/10/0	3/30/0
DS	C5	MIL-STD750-2	-	5	Die Shear	MIL-STD750-2 Method 2017	1 Step	1/5/0	1/5/0	1/5/0	1/5/0	1/5/0	1/5/0	1/5/0	3/15/0
RSH	C8	JESD22B107	-	30	Solder Heat	260C, 10 seconds	1 Step	1/30/0	-	-	-	-	-	-	1/30/0
SD	C10	JEDEC J-STD-002	-	15	PB Solderability	Precondition w.155C Dry Bake (4 hrs +/- 15 minutes)	1 Step	-	-	-	-	-	-	-	1/10/0
SD	C10	JEDEC J-STD-002	-	15	PB-Free Solderability	Precondition w.155C Dry Bake (4 hrs +/- 15 minutes)	1 Step	1/15/0	-	-	-	-	-	-	1/10/0
Test Group D - Die Fabrication Reliability Tests															
Test Group E - Electrical Verification Tests															
EV	E0	JESD22B101	3	1000	Visual/Mechanical	Per JESD22 B-101	1 Step	1/1000/0	-	-	1/1000/0	-	-	1/1000/0	3/3000/0
ESD	E3	AEC Q101-001	3	10	ESD HBM	Room Temp	2000 Volts	1/10/0	-	-	-	-	-	-	1/80/0
ESD	E4	AEC Q101-005	3	10	ESD CDM	Room Temp	500 Volts	-	-	-	-	-	-	-	1/60/0
ESD	E4	AEC Q101-005	3	10	ESD CDM	Room Temp	750 Volts	1/10/0	-	-	-	-	-	-	-
Type	**#**	**Test Spec**	**Min Lot Qty**	**SS / Lot**	**Test Name**	**Condition**	**Duration**	**Qual Device**	**Qual Device**	**Qual Device**	**Qual Device**	**Qual Device**	**Qual Device**	**Qual Device**	**QBS Reference**

- Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, HTSL, and IOL, as applicable
- Passing results reflect shift analysis per Q101 requirements

Ambient Operating Temperature by Automotive Grade Level:

- Grade 0 [or E]: -40C to +150C
- Grade 1 [or Q]: -40C to +125C
- Grade 2 [or T]: -40C to +105C
- Grade 3 [or U]: -40C to +85C

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):

- Room/Hot/Cold: HTRB, ED
- Room/Hot: THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU
- Room: AC/UHST

Quality and Environmental data is available at TI's external Web site: http://www.ti.com/

TI Qualification ID: R-CHG-2403-055

In performing change qualifications, Texas Instruments follows integrated circuit industry standards in performing defect mechanism analysis and failure mechanism-based accelerated environmental testing to ensure wafer fab process, assembly process and product quality and

reliability. As encouraged by these standards, TI uses both product-specific and generic (family) data in qualifying its changes. For devices to be categorized as a 'product qualification family' for generic data purposes, they must share similar product, wafer fab process and assembly process elements. The applicability of generic data (also known at TI as Qualification by Similarity (QBS)) is determined by the Reliability Engineering function following these industry standards. Generic data is shown in the qualification report in columns titled "QBS Process" (for wafer fab process), "QBS Package" (for assembly process) and "QBS Product" (for product family).

ZVEI ID: SEM-PW-13, SEM-PA-18, SEM-PA-07, SEM-PA-05

For questions regarding this notice, e-mails can be sent to the Change Management team or your local Field Sales Representative.